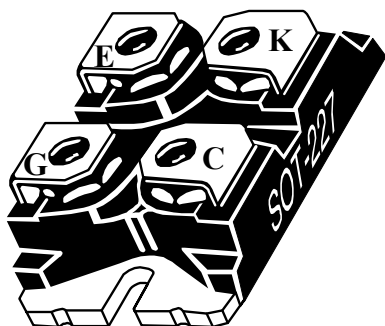
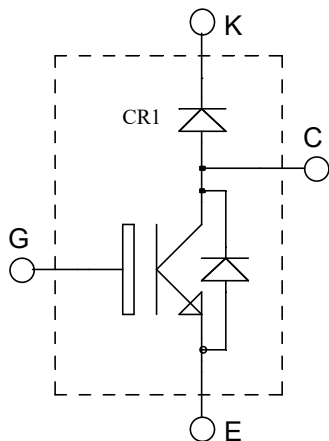


Boost chopper
High speed Trench + Field Stop IGBT4

$V_{CES} = 1200V$
 $I_C = 40A @ T_c = 80^\circ C$



Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction
- Brake switch

Features

- **High speed Trench + Field Stop IGBT 4 Technology**
 - Low voltage drop
 - Low leakage current
 - Low switching losses
 - RBSOA and SCSOA rated
- **SiC Schottky Diode (CR1)**
 - Zero reverse recovery
 - Zero forward recovery
 - Temperature Independent switching behavior
 - Positive temperature coefficient on VF
- Very low stray inductance
- High level of integration

Benefits

- Low conduction losses
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant

All ratings @ $T_j = 25^\circ C$ unless otherwise specified

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	1200	V
I_C	Continuous Collector Current	$T_C = 25^\circ C$ 80	A
		$T_C = 80^\circ C$ 40	
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ C$ 160	
V_{GE}	Gate – Emitter Voltage	± 20	V
P_D	Power Dissipation	$T_C = 25^\circ C$ 312	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^\circ C$ 80A @ 1100V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

Electrical Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$			25	μA
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15V$ $I_C = 40A$	$T_j = 25^\circ C$ $T_j = 150^\circ C$	1.7 2.6	2.4	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 1mA$	5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = \pm 20V, V_{CE} = 0V$			120	nA

Dynamic Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
C_{ies}	Input Capacitance	$V_{GE} = 0V$		2300		pF
C_{oes}	Output Capacitance	$V_{CE} = 25V$		150		
C_{res}	Reverse Transfer Capacitance	$f = 1MHz$		130		
Q_G	Gate charge	$V_{GE} = 15V, I_C = 40A$ $V_{CE} = 960V$		185		nC
$T_{d(on)}$	Turn-on Delay Time	Resistive Switching ($25^\circ C$) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 40A$ $R_G = 12\Omega$		30		ns
T_r	Rise Time			57		
$T_{d(off)}$	Turn-off Delay Time			290		
T_f	Fall Time			16		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ($150^\circ C$) $V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 40A$ $R_G = 12\Omega$		30		ns
T_r	Rise Time			49		
$T_{d(off)}$	Turn-off Delay Time			366		
T_f	Fall Time			48		
E_{on}	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 600V$ $I_C = 40A$ $R_G = 12\Omega$	$T_j = 25^\circ C$ $T_j = 150^\circ C$	1.9 2.25		mJ
E_{off}	Turn-off Switching Energy		$T_j = 25^\circ C$ $T_j = 150^\circ C$	1.2 2.25		
I_{sc}	Short Circuit data	$V_{GE} \leq 15V ; V_{Bus} = 600V$ $t_p \leq 10\mu s ; T_j = 150^\circ C$		150		A

Chopper SiC diode ratings and characteristics (CR1)

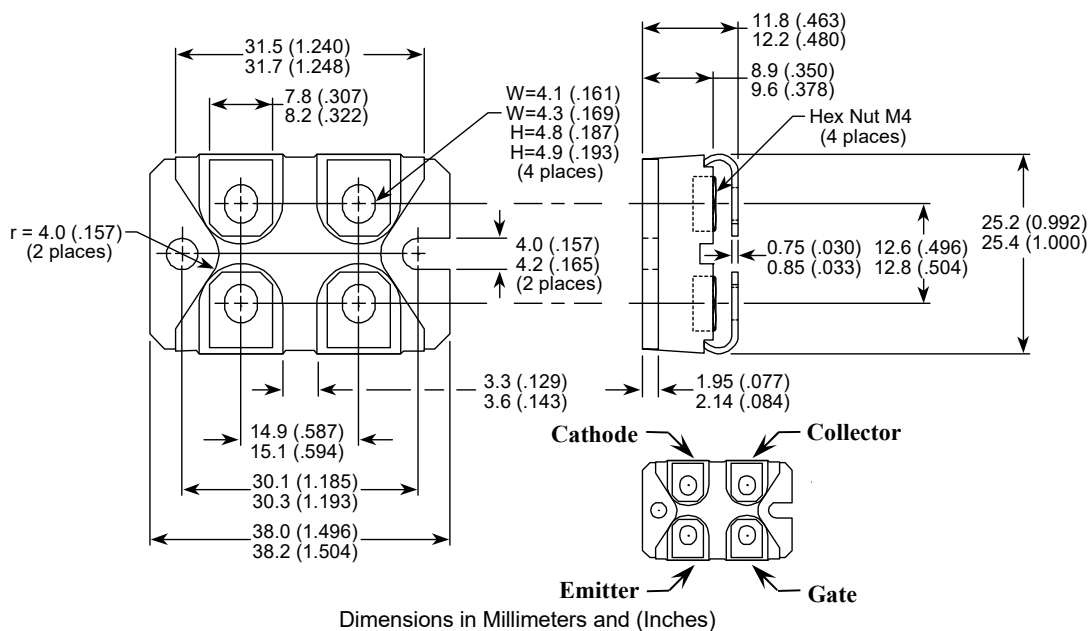
<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>	<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		1200			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1200V$	$T_j = 25^\circ C$ $T_j = 175^\circ C$	64 112	400 2000	μA
I_F	DC Forward Current		$T_c = 100^\circ C$	20		A
V_F	Diode Forward Voltage	$I_F = 20A$	$T_j = 25^\circ C$ $T_j = 175^\circ C$	1.6 2.3	1.8 3	V
Q_C	Total Capacitive Charge	$I_F = 20A, V_R = 600V$ $di/dt = 1000A/\mu s$		80		nC
C	Total Capacitance	$f = 1MHz, V_R = 200V$ $f = 1MHz, V_R = 400V$		192 138		pF

Thermal and package characteristics

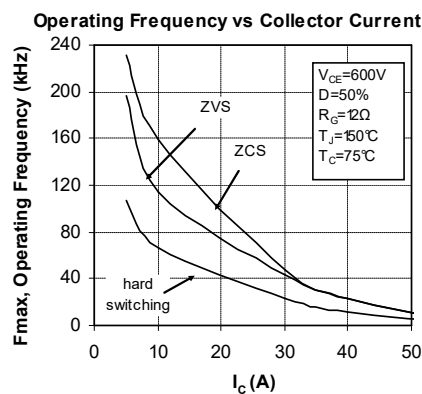
Symbol Characteristic

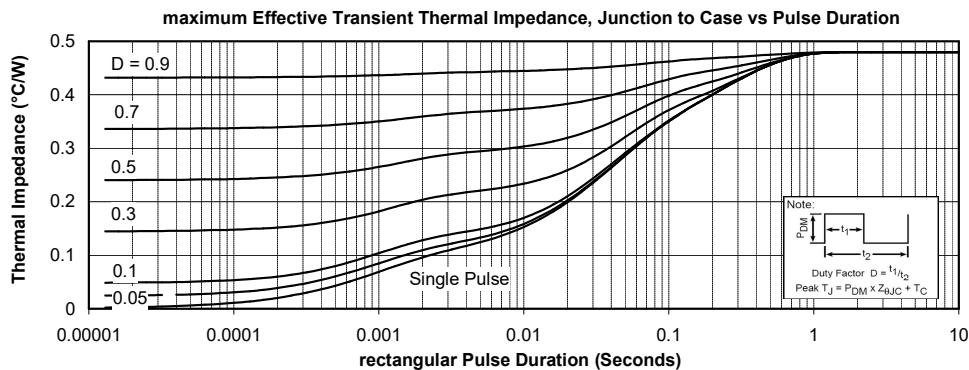
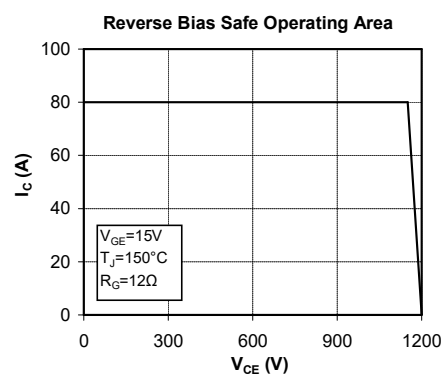
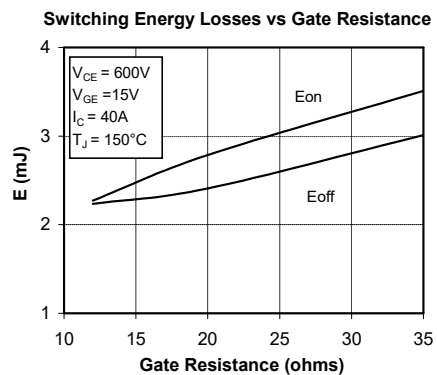
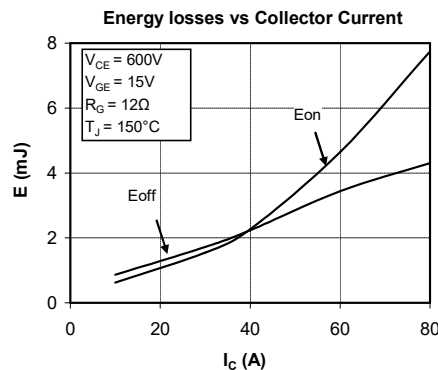
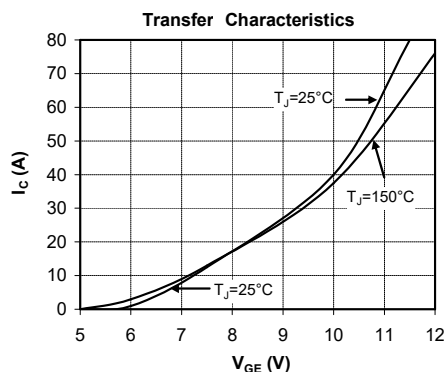
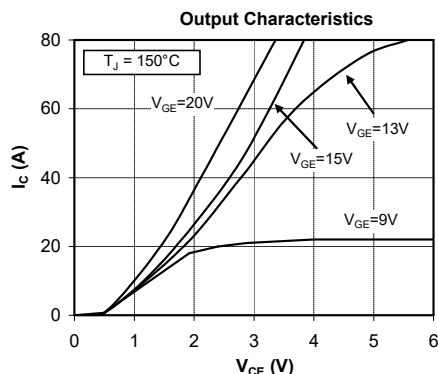
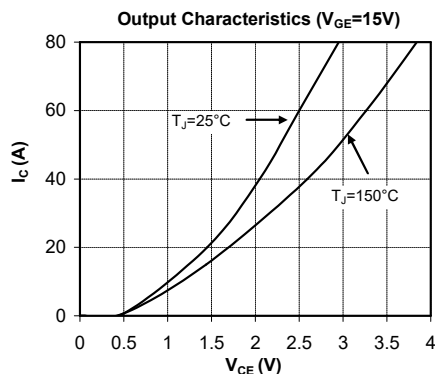
		Min	Typ	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance	IGBT		0.48	°C/W
		SiC Diode		0.8	
R_{thJA}	Junction to Ambient (IGBT & Diode)			20	
V_{ISOL}	RMS Isolation Voltage, any terminal to case $t = 1$ min, 50/60Hz	2500			V
T_J, T_{STG}	Storage Temperature Range	-55		150	°C
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)			1.5	N.m
Wt	Package Weight		29.2		g

Package Outline

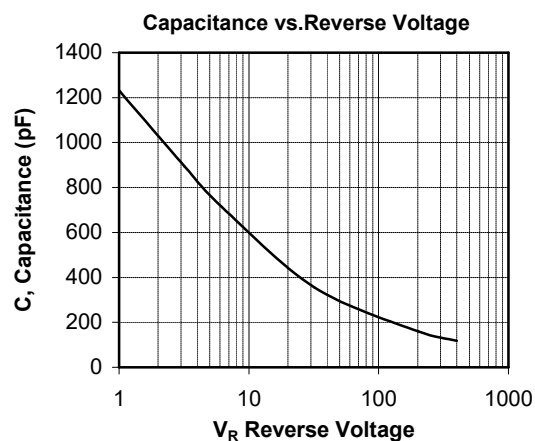
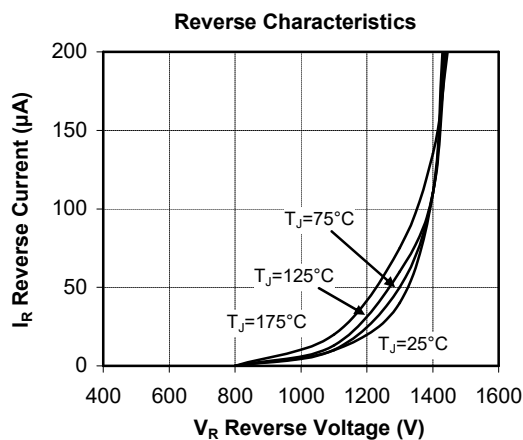
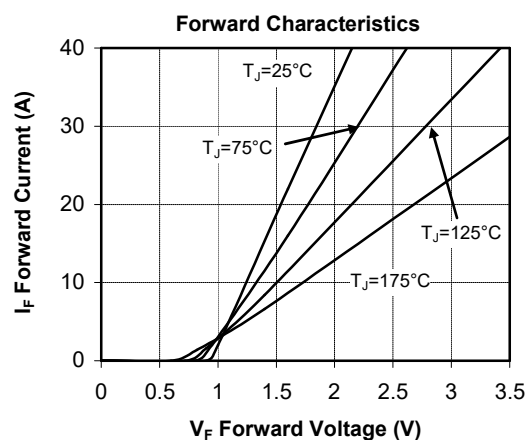
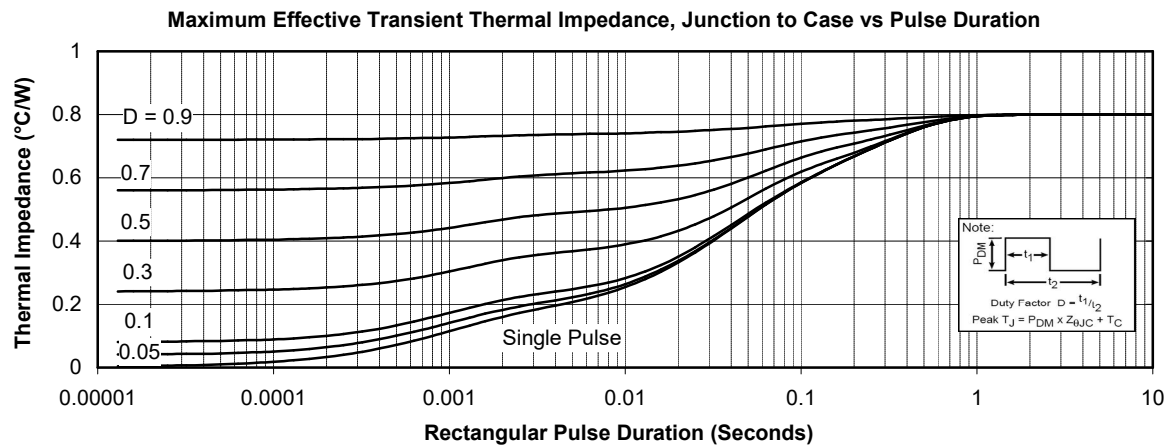


Typical IGBT Performance Curve





Typical chopper SiC diode Performance Curve



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